

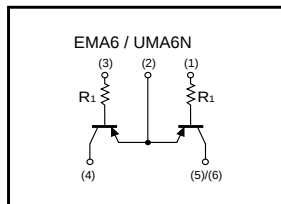
Emitter common (dual digital transistors)

EMA6 / UMA6N

●Feature

1) Two DTA114T chips in a EMT or UMT package.

●Equivalent circuit



●Package, marking, and packaging specifications

Type	EMA6	UMA6N
Package	EMT5	UMT5
Marking	A6	A6
Code	T2R	TR
Basic ordering unit (pieces)	8000	3000

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CB0}	-50	V
Collector-emitter voltage	V_{CE0}	-50	V
Emitter-base voltage	V_{EB0}	-5	V
Collector current	I_C	-100	mA
Collector power dissipation	P_C	150(TOTAL)	mW *1
Junction temperature	T_J	150	°C
Storage temperature	T_{stg}	-55~+150	°C

*1 120mW per element must not be exceeded.

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CB0}	-50	-	-	V	$I_C = -50\mu A$
Collector-emitter breakdown voltage	BV_{CE0}	-50	-	-	V	$I_C = -1mA$
Emitter-base breakdown voltage	BV_{EB0}	-5	-	-	V	$I_E = -50\mu A$
Collector cutoff current	I_{CBO}	-	-	-0.5	μA	$V_{CB} = -50V$
Emitter cutoff current	I_{EBO}	-	-	-0.5	μA	$V_{EB} = -4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	-0.3	V	$I_C/I_E = -5mA/-0.5mA$
DC current transfer ratio	h_{FE}	100	250	600	-	$V_{CE}/I_C = -5V/-1mA$
Transition frequency	f_T	-	250	-	MHz	$V_{EB} = 10V, I_E = -5mA, f = 100MHz$ *
Input resistance	R_i	32.9	47	61.1	k Ω	-

* Transition frequency of the device.

●External dimensions (Units : mm)

